

60 V, 320 mA N-channel Trench MOSFET Rev. 1 — 12 August 2011

Product data sheet

Product profile 1.

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

1.4 Quick reference data

- ESD protection up to 1.5 kV
- AEC-Q101 qualified
- Low-side loadswitch
- Switching circuits

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	60	V
V_{GS}	gate-source voltage		-20	-	20	V
I _D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C	<u>[1]</u> _	-	320	mA
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 320 mA; T _j = 25 °C	-	1	1.6	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 320 mA N-channel Trench MOSFET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		5
2	S	source		
3	D	drain	1 ☐ 2 SOT323 (SC-70)	G S 017aaa255

3. Ordering information

Table 3.	able 3. Ordering information			
Type number		Package		
		Name	Description	Version
BSS138BK	W	SC-70	plastic surface-mounted package; 3 leads	SOT323

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
BSS138BKW	AD%

[1] % = placeholder for manufacturing site code.

Limiting values 5.

Table 5. **Limiting values**

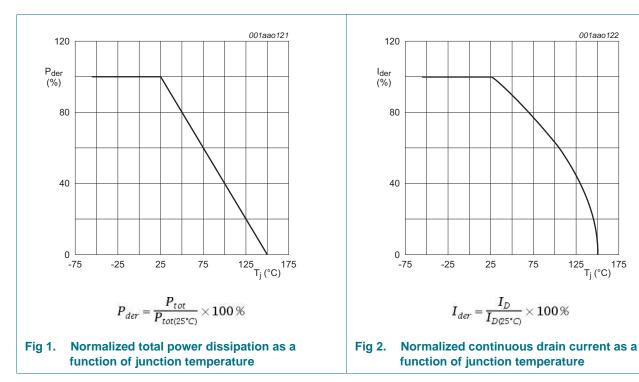
In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
drain-source voltage	$T_i = 25 \text{ °C}$	-	60	V
gate-source voltage		-20	20	V
drain current	V _{GS} = 10 V; T _{amb} = 25 °C	<u>[1]</u> _	320	mA
	V_{GS} = 10 V; T_{amb} = 100 °C	<u>[1]</u> -	210	mA
peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$	-	1.2	А
total power dissipation	T _{amb} = 25 °C	[2] _	260	mW
		<u>[1]</u> _	310	mW
	T _{sp} = 25 °C	-	830	mW
junction temperature		-55	150	°C
ambient temperature		-55	150	°C
storage temperature		-65	150	°C
diode				
source current	T _{amb} = 25 °C	<u>[1]</u> _	320	mA
n rating				
electrostatic discharge voltage	HBM	<u>[3]</u>	1500	V
	drain-source voltage gate-source voltage drain current peak drain current total power dissipation junction temperature ambient temperature storage temperature diode source current n rating	$ \begin{array}{c} \mbox{drain-source voltage} & T_{j} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{gate-source voltage} & & \\ \mbox{drain current} & & \\ \mbox{V}_{GS} = 10 \ ^{\circ}\mbox{,} \ T_{amb} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{V}_{GS} = 10 \ ^{\circ}\mbox{,} \ T_{amb} = 100 \ ^{\circ}\mbox{C} & \\ \mbox{V}_{GS} = 10 \ ^{\circ}\mbox{,} \ T_{amb} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{peak drain current} & T_{amb} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{total power dissipation} & T_{amb} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{T}_{amb} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{T}_{amb} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{T}_{sp} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{Junction temperature} & \\ \mbox{storage temperature} & \\ \mbox{diode} & \\ \mbox{source current} & T_{amb} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{T}_{amb} = 25 \ ^{\circ}\mbox{C} & \\ \mbox{T}_{$	$\begin{tabular}{ c c c c } \hline \mbox{drain-source voltage} & $T_j = 25 \ ^{\circ}\ C & -20 \\ \hline \mbox{gate-source voltage} & $V_{GS} = 10 \ V; \ T_{amb} = 25 \ ^{\circ}\ C & 11 - $$$$$$$$$$$$$$$$$$V_{GS} = 10 \ V; \ T_{amb} = 100 \ ^{\circ}\ C & 11 - $$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint. [2]

Measured between all pins. [3]



125 175 T_j (°C)

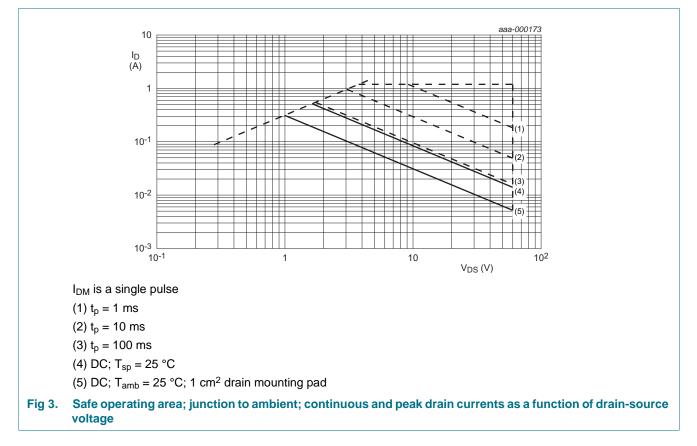
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Product data sheet

BSS138BKW

60 V, 320 mA N-channel Trench MOSFET



6. Thermal characteristics

Table 6. Thermal characteristics

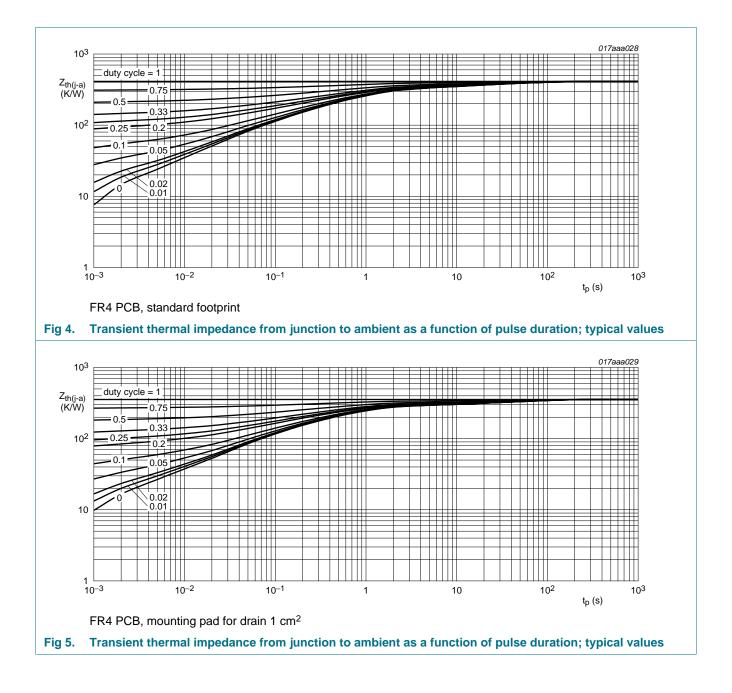
Symbol	Parameter Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient in free air	<u>[1]</u> _	415	480	K/W
		[2] _	350	400	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point	-	-	150	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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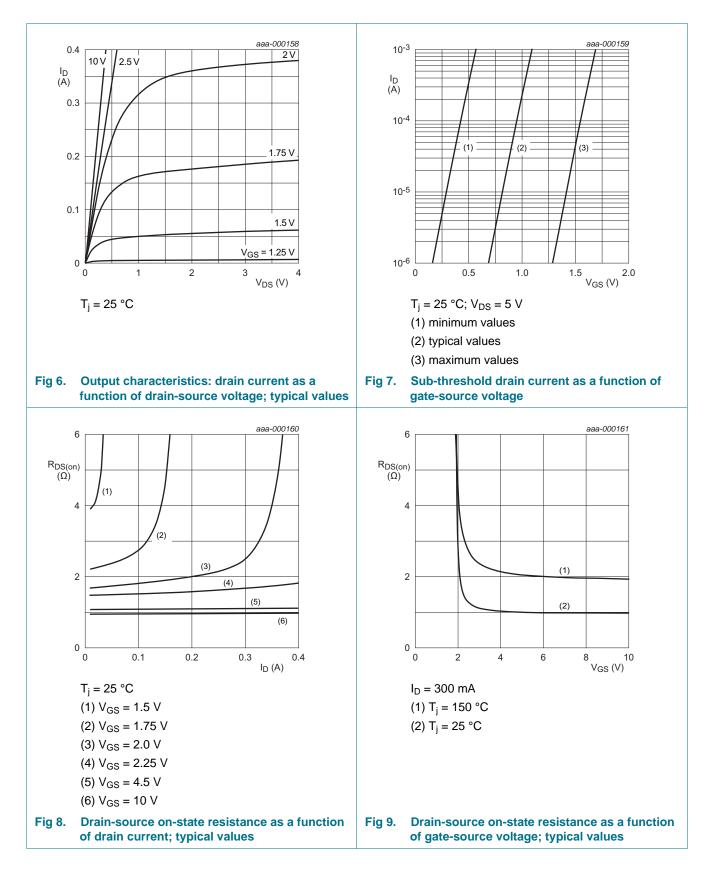


7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	60	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	0.48	1.1	1.6	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; \text{ V}_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	10	μΑ
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μΑ
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 320 mA; T _j = 25 °C	-	1	1.6	Ω
		V_{GS} = 10 V; I _D = 320 mA; T _j = 150 °C	-	2	3.2	Ω
		V_{GS} = 4.5 V; I _D = 200 mA; T _j = 25 °C	-	1.1	2.2	Ω
		V_{GS} = 2.5 V; I _D = 10 mA; T _j = 25 °C	-	1.4	6.5	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 200 mA; T_j = 25 °C	-	700	-	mS
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; \text{ I}_{D} = 300 \text{ mA}; \text{ V}_{GS} = 4.5 \text{ V};$	-	0.6	0.7	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}$	-	0.1	-	nC
Q _{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	$V_{DS} = 10 \text{ V}; \text{ f} = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	42	56	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}$	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 250 \Omega; V_{GS} = 10 \text{ V}; \label{eq:VDS}$	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	38	76	ns
t _f	fall time		-	20	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 300 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.8	1.2	V

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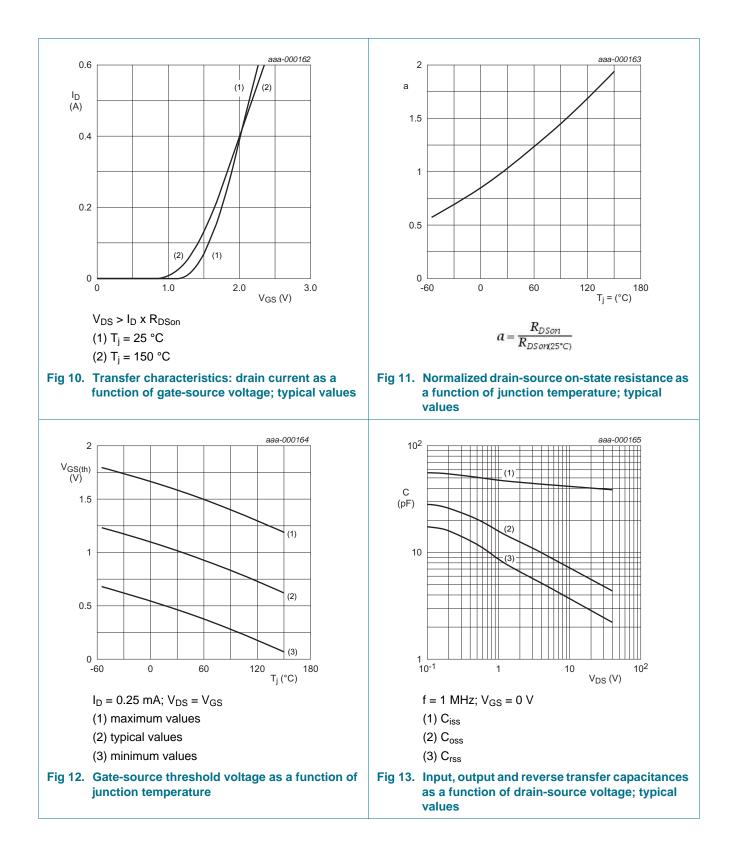


BSS138BKW

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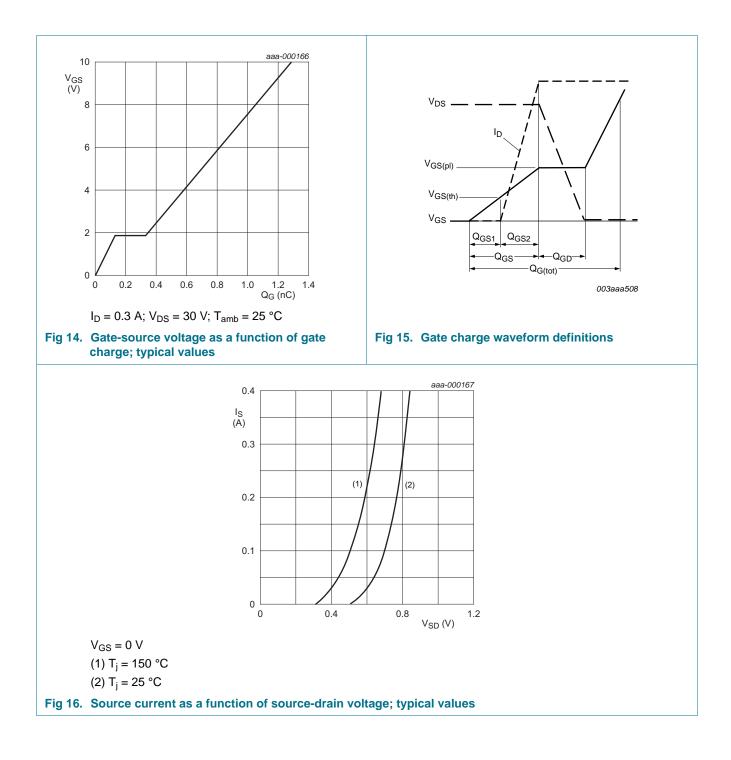
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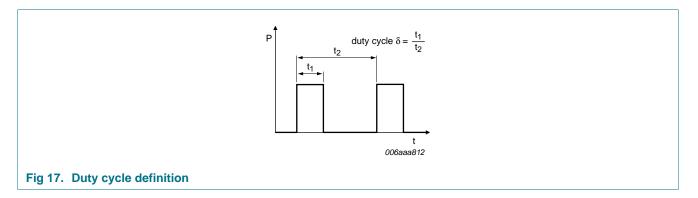
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60 V, 320 mA N-channel Trench MOSFET



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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

BSS138BKW

60 V, 320 mA N-channel Trench MOSFET

9. Package outline

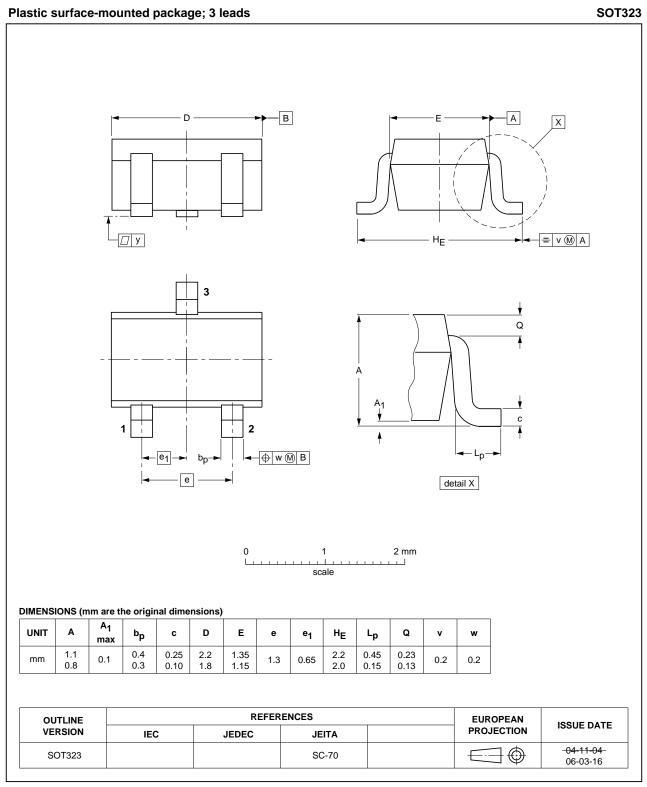
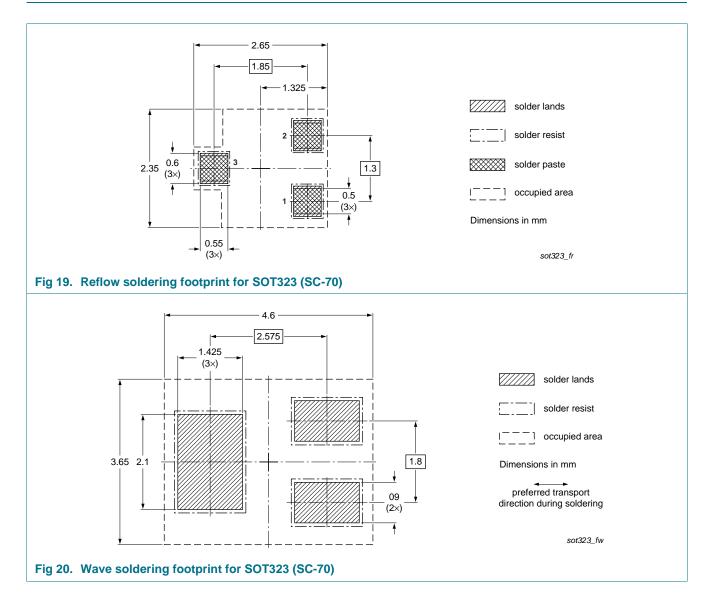


Fig 18. Package outline SOT323 (SC-70)

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60 V, 320 mA N-channel Trench MOSFET

10. Soldering



11. Revision history

Table 8.	Revision history				
Document	ID	Release date	Data sheet status	Change notice	Supersedes
BSS138BK\	W v.1	20110812	Product data sheet	-	-

BSS138BKW

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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60 V, 320 mA N-channel Trench MOSFET

14. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking
5	Limiting values
6	Thermal characteristics4
7	Characteristics6
8	Test information10
8.1	Quality information10
9	Package outline11
10	Soldering12
11	Revision history13
12	Legal information14
12.1	Data sheet status14
12.2	Definitions14
12.3	Disclaimers
12.4	Trademarks15
13	Contact information15

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